

N-Channel Super Junction Power MOSFET IV

General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

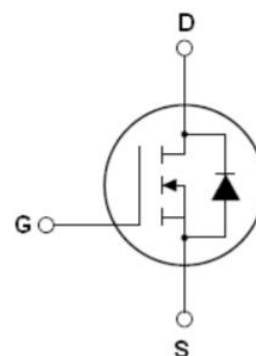
Features

- New technology for high voltage device
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)

$V_{DS\ min@T_{jmax}}$	550	V
$R_{DS(ON)TYP.}$	470	mΩ
I_D	7.5	A
Q_g	10	nC



Schematic diagram

Package Marking And Ordering Information

Device	Device Package	Marking
NCE50N540K	TO-252	NCE50N540K



TO-252

Table 1. Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	500	V
Gate-Source Voltage ($V_{DS}=0V$), AC ($f>1\text{ Hz}$)	V_{GS}	± 30	V
Gate-Source Voltage ($V_{DS}=0V$), DC	V_{GS}	± 20	V
Continuous Drain Current at $T_c=25^\circ\text{C}$	$I_{D(DC)}$	7.5	A
Continuous Drain Current at $T_c=100^\circ\text{C}$	$I_{D(DC)}$	5.25	A
Pulsed drain current (Note 1)	$I_{DM (pluse)}$	22.5	A
Maximum Power Dissipation($T_c=25^\circ\text{C}$)	P_D	74	W
Derate above 25°C		0.49	W/ $^\circ\text{C}$
Single pulse avalanche energy (Note 2)	E_{AS}	16	mJ
Single pulse avalanche current (Note 2)	I_{AS}	2	A
Repetitive Avalanche energy, t_{AR} limited by T_{jmax} (Note 1)	E_{AR}	0.9	mJ
Reverse diode dv/dt , $V_{DS} \leq 480\text{ V}$, $I_{SD} < I_D$	dv/dt	15	V/ns
Drain Source voltage slope, $V_{DS} \leq 480\text{ V}$	dv/dt	50	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55...+175	$^\circ\text{C}$

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R_{thJC}	2.02	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient (Maximum)	R_{thJA}	62	$^{\circ}\text{C}/\text{W}$

Table 3. Electrical Characteristics (TA=25 $^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250uA	500			V
Zero Gate Voltage Drain Current(Tc=25℃)	I _{DSS}	V _{DS} =500V,V _{GS} =0V			1	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I _{DSS}	V _{DS} =500V,V _{GS} =0V			50	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V			±200	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250uA	3		4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =3.5A		470	540	mΩ
Dynamic Characteristics						
Gate Resistance	R _g	F=1MHZ, D-S short		60		Ω
Input Capacitance	C _{iss}	V _{DS} =50V,V _{GS} =0V, F=1MHz		402		pF
Output Capacitance	C _{oss}			21		pF
Reverse Transfer Capacitance	C _{rss}			3		pF
Total Gate Charge	Q _g	V _{DS} =400V,I _D =3.5A, V _{GS} =10V		10	12	nC
Gate-Source Charge	Q _{gs}			1.66		nC
Gate-Drain Charge	Q _{gd}			6.09		nC
Gate plateau voltage	V _{gp}			4.7		V
Switching times						
Turn-on Delay Time	t _{d(on)}	V _{DD} =380V,I _D =4A, R _G =4Ω,V _{GS} =10V		8		nS
Turn-on Rise Time	t _r			10		nS
Turn-Off Delay Time	t _{d(off)}			41		nS
Turn-Off Fall Time	t _f			9		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I _{SD}	T _C =25℃			7.5	A
Pulsed-Source-drain current(Body Diode)	I _{SDM}				22.5	A
Forward on voltage	V _{SD}	T _J =25℃,I _{SD} =7.5A,V _{GS} =0V		1.0	1.2	V
Reverse Recovery Time	t _{rr}	T _J =25℃,I _F 4A, di/dt=100A/μs		185		nS
Reverse Recovery Charge	Q _{rr}			1.5		uC
Peak reverse recovery current	I _{rrm}			12		A

Notes: 1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. $T_j=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, R_G=25\Omega$

Figure1. Safe operating area



Figure7. BV_{DSS} vs Junction Temperature

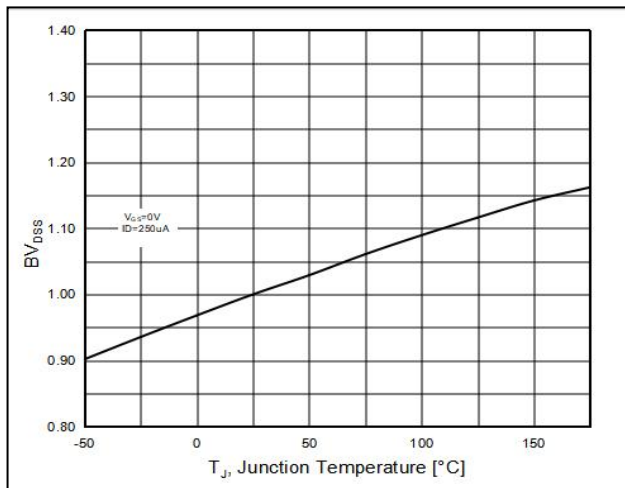


Figure8. Maximum I_D vs Junction Temperature

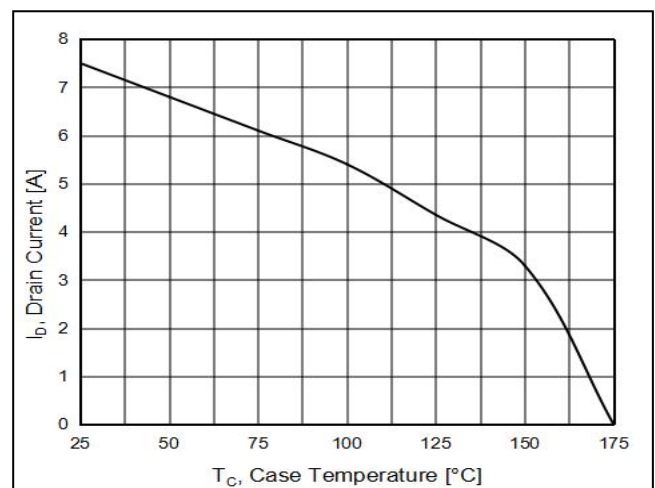


Figure9. Gate charge waveforms

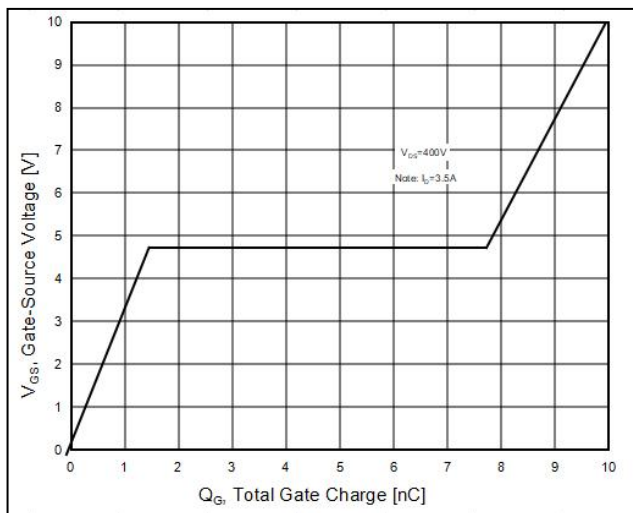
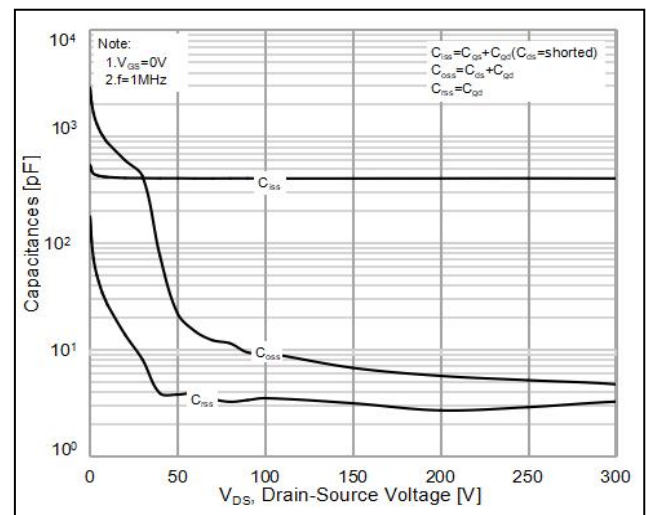
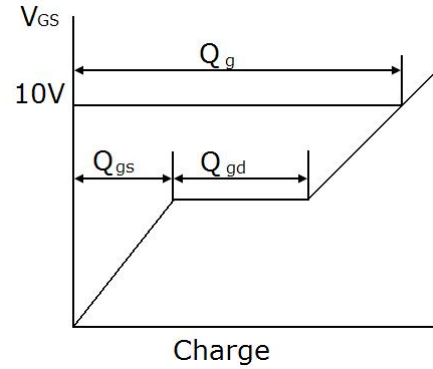


Figure10. Capacitance

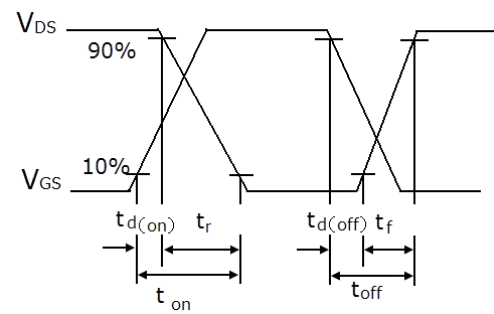


Test circuit

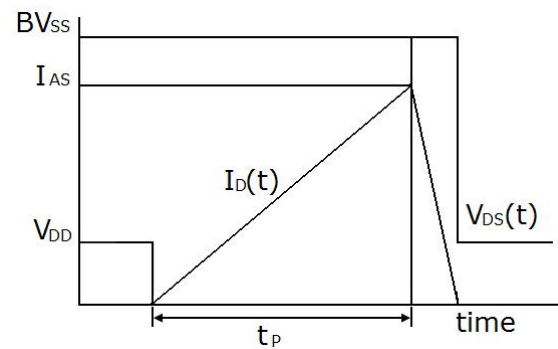
1) Gate charge test circuit & Waveform



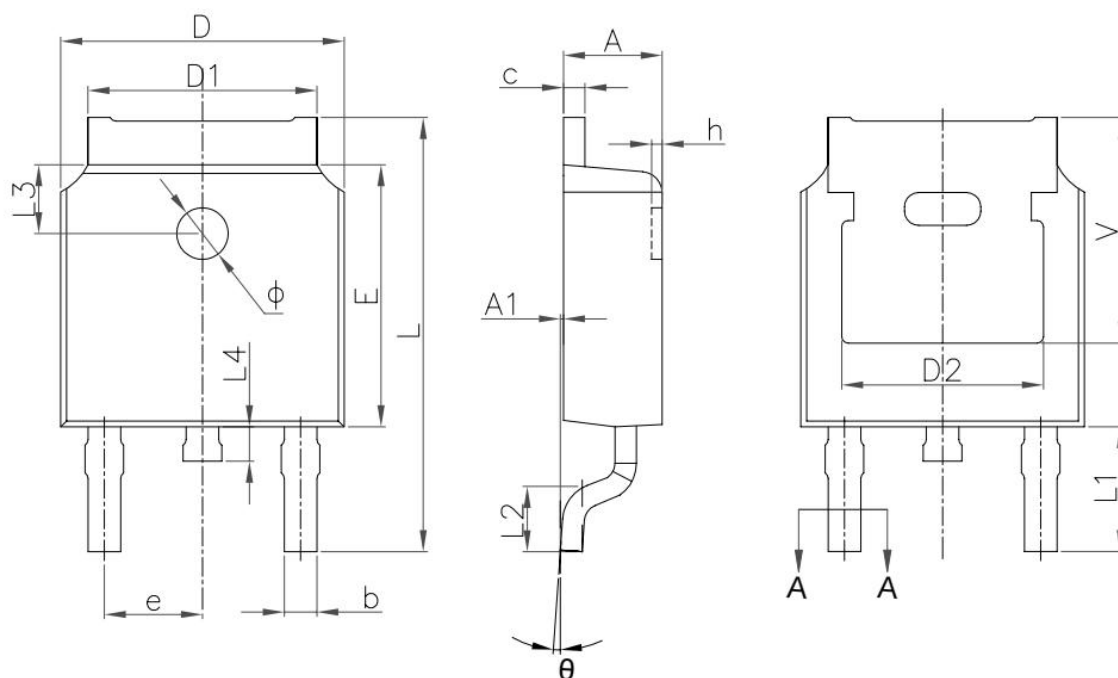
2) Switch Time Test Circuit:



3) Unclamped Inductive Switching Test Circuit & Waveforms



TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.20	2.40	0.087	0.094
A1	0.00	0.13	0.000	0.005
b	0.66	0.86	0.026	0.033
b1	0.73	0.79	0.029	0.031
c	0.46	0.58	0.018	0.023
c1	0.50	0.52	0.020	0.020
D	6.50	6.70	0.256	0.264
D1	5.10	5.46	0.201	0.215
D2	4.83 REF		0.19REF	
E	6.00	6.20	0.236	0.244
e	2.19	2.39	0.086	0.094
L	9.80	10.40	0.386	0.409
L1	2.90 REF		0.11REF	
L2	1.40	1.70	0.055	
L3	1.60 REF		0.06REF	
L4	0.60	1.00	0.024	0.039
Φ	1.10	1.30	0.043	0.051
θ	0°	8°	0°	8°
h	0.00	0.30	0.000	0.012

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